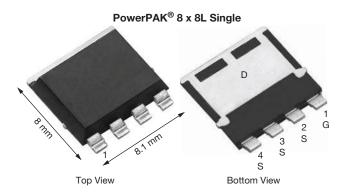


www.vishay.com

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10 \text{ V}$	0.0015
I _D (A)	200
Configuration	Single
Package	PowerPAK 8 x 8L

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





G G
N-Channel MOSFET

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	40		
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain current	T _C = 25 °C ^a	1	200		
Continuous drain current	T _C = 125 °C	I _D	141		
Continuous source current (diode conducti	I _S	136	А		
Pulsed drain current ^b		I _{DM}		600	
Single pulse avalanche current		I _{AS}		70	
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	245	mJ	
Maximum navar dissination	T _C = 25 °C	Б	150	14/	
Maximum power dissipation	T _C = 125 °C	P_{D}	50	W	
Operating junction and storage temperatur	T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak tempera		260	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient F	CB mount c	R _{thJA}	50	°C/W
Junction-to-case (drain)		R _{thJC}	1	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μA	2.5	3	3.5] V
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	500	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	100	-	-	Α
		V _{GS} = 10 V	I _D = 20 A	-	0.0011	0.0015	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0021	Ω
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0025	1
Forward transconductance b	9fs	V _{DS} = 15 V, I _D = 15 A		-	122	-	S
Dynamic ^b							
Input capacitance	C _{iss}			-	11 367	14 780	
Output capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	6000	7800	pF
Reverse transfer capacitance	C _{rss}			-	615	800	
Total gate charge ^c	Qg			-	125	165	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_D = 10 \text{ A}$	-	35	-	nC
Gate-drain charge ^c	Q_{gd}			-	13	-	
Gate resistance	R _g		f = 1 MHz	0.45	0.99	1.50	Ω
Turn-on delay time ^c	t _{d(on)}			-	22	32	
Rise time ^c	t _r	V_{DD}	= 20 V, $R_L = 2 \Omega$	-	8	14]
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 A$,	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	52	73	ns
Fall time ^c	t _f			-	14	20]
Source-Drain Diode Ratings and Cha	aracteristics b						
Pulsed current ^a	I _{SM}			-	-	200	Α
Forward voltage	V _{SD}	le -	50 A, V _{GS} = 0 V	_	0.8	1.1	V

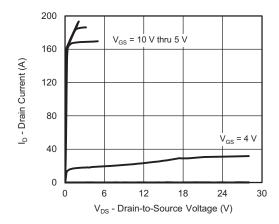
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

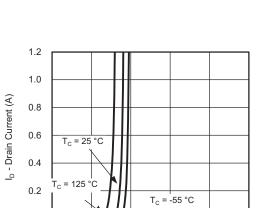
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics



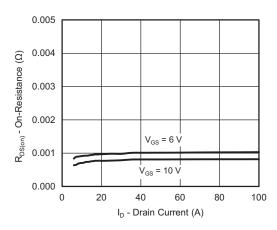
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Transfer Characteristics

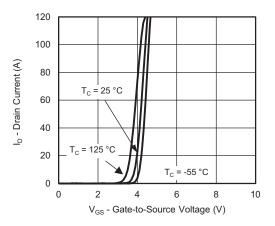
V_{GS} - Gate-to-Source Voltage (V)

6

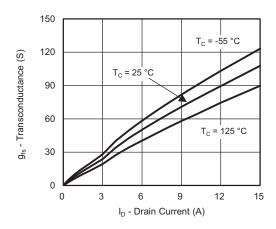
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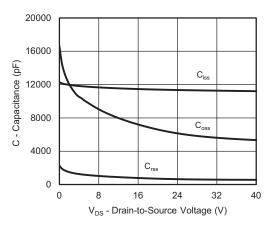
On-Resistance vs. Drain Current



Transfer Characteristics



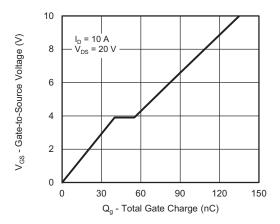
Transconductance



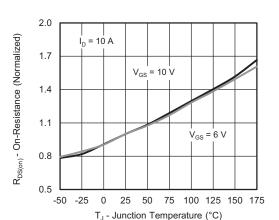
Capacitance



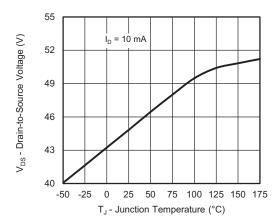
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



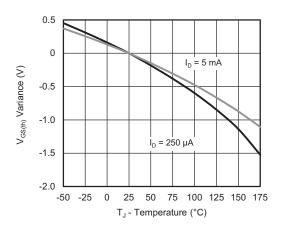
Gate Charge



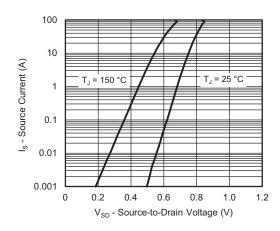
On-Resistance vs. Junction Temperature



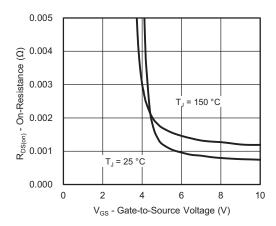
Drain Source Breakdown vs. Junction Temperature



Threshold Voltage



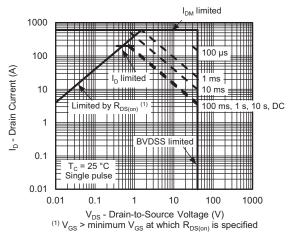
Source Drain Diode Forward Voltage



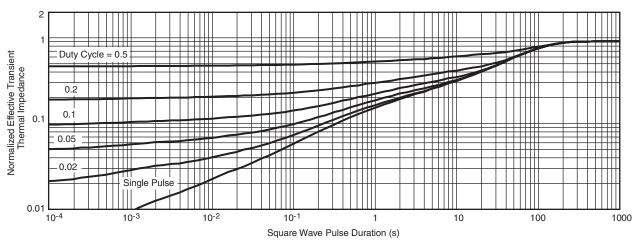
On-Resistance vs. Gate-to-Source Voltage



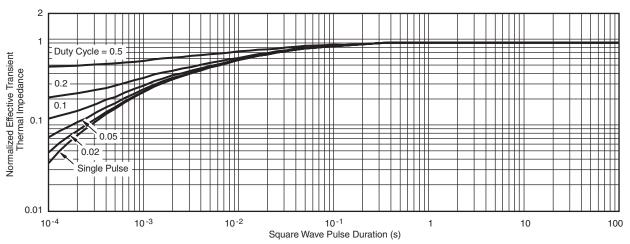
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

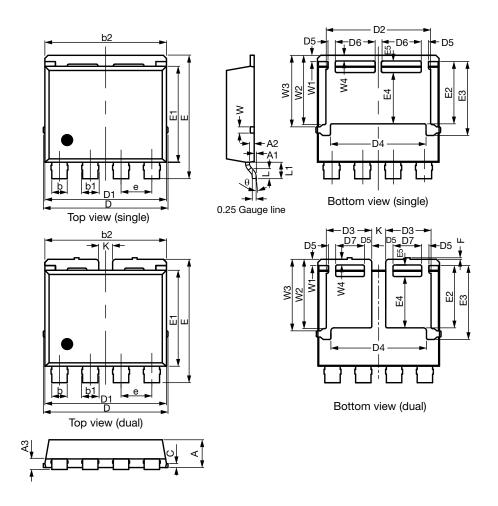


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg271828.



PowerPAK® 8 x 8L Case Outline



DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A2	0.25	0.30	0.35	0.010	0.012	0.014	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
D5	0.37	0.47	0.57	0.015	0.019	0.022	
D6	2.49	2.59	2.69	0.098	0.102	0.106	
D7	1.76	1.86	1.96	0.069	0.073	0.077	

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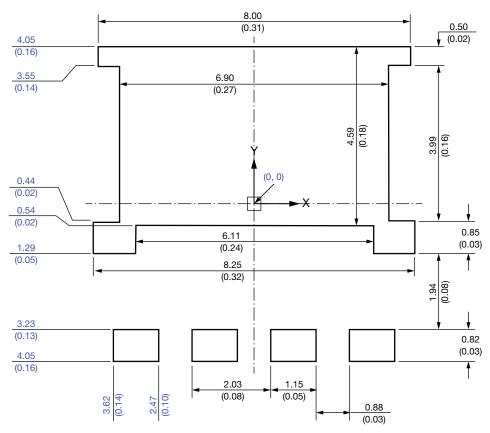
DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
E	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	

C17-1388-Rev. B, 16-Oct-17

DWG: 6026



Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

· Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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